



74LCX16541

LOW VOLTAGE CMOS 16-BIT BUS BUFFER (3-STATE) WITH 5V TOLERANT INPUTS/OUTPUTS (NON INVERTED)

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED:
 $t_{PD} = 4.1 \text{ ns (MAX.)}$ at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu A \text{ (MAX.)}$ at $T_A = 25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC} \text{ (MIN.)}$
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC(OPER)} = 2V \text{ to } 3.6V \text{ (1.5V Data Retention)}$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 16541
- IMPROVED LATCH-UP IMMUNITY
- ESD PERFORMANCE:
 $HBM > 2000V \text{ (MIL STD 883 method 3015)}$
 $MM > 200V$

DESCRIPTION

The 74LCX16541 is an advanced high-speed CMOS 16-BIT BUS BUFFER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring CMOS technology.

This is composed of two 8 bit sections with separate output-enable signals. For either 8-bit buffer section, the 3-STATE control gate operates as a two input AND such that if either $\overline{nG1}$ and $\overline{nG2}$ are high, all outputs are in the high impedance state. This device is designed to be used with 3 state memory address drivers, etc.

It has same speed performance at 3.3V than 5V AC/ACT family, combined with a lower power consumption.

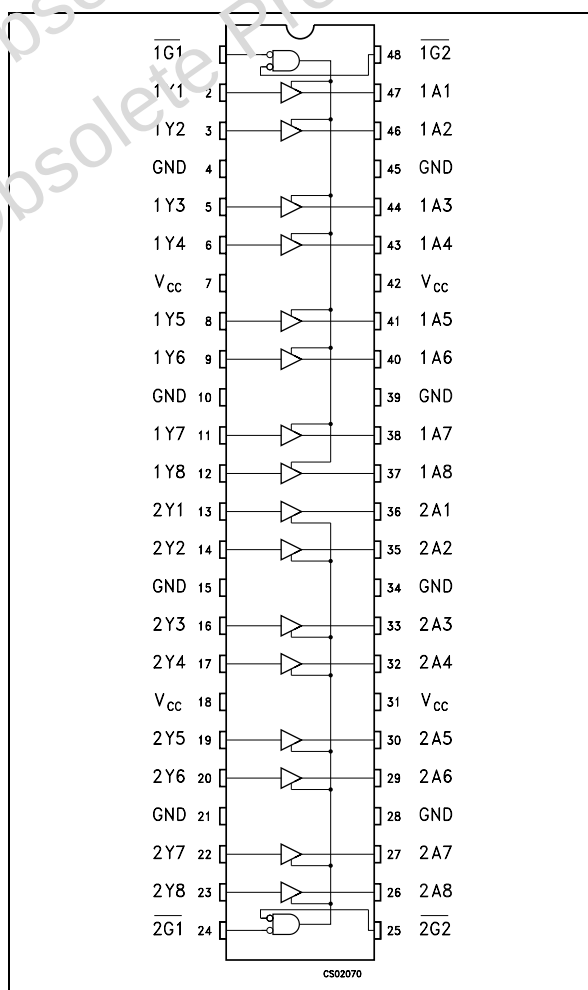
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.



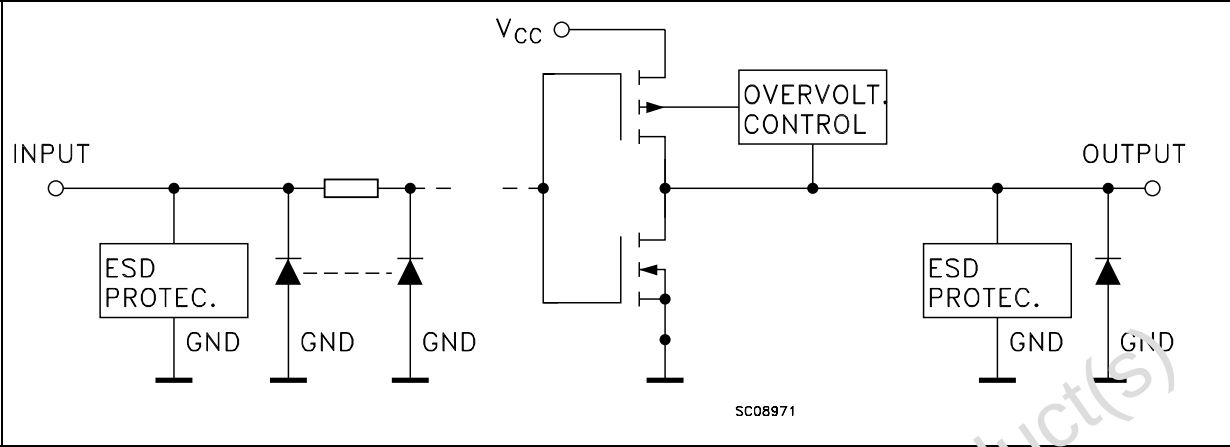
ORDER CODES

PACKAGE	TUBE	T & F
TSSOP		74LCX16541TTR

PIN CONNECTION



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

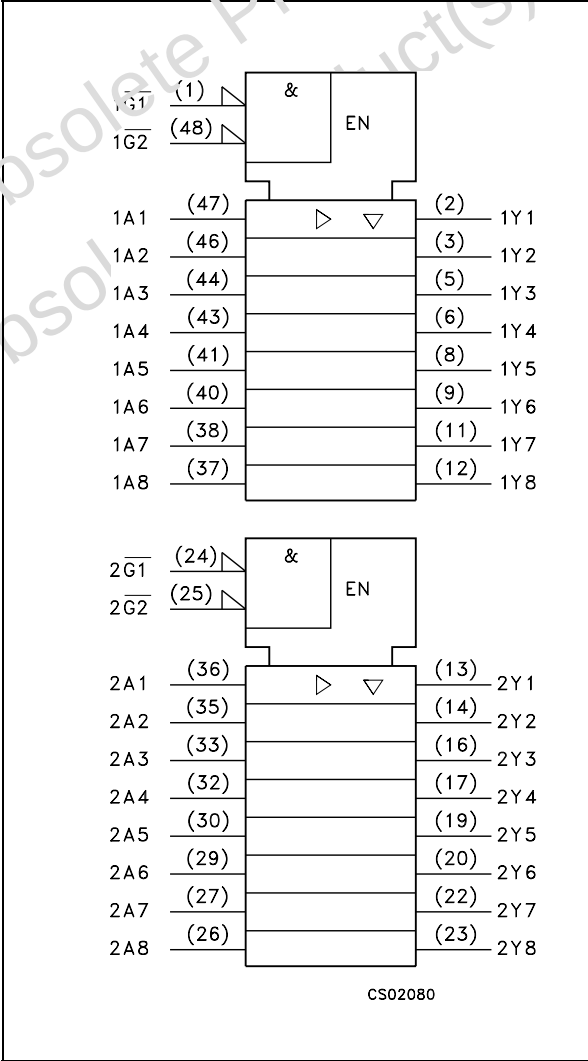
PIN No	SYMBOL	NAME AND FUNCTION
1, 48	1G1, 1G2	Output Enable Inputs
2, 3, 5, 6, 8, 9, 11, 12	1Y1 to 1Y8	Data Outputs
13, 14, 16, 17, 19, 20, 22, 23	2Y1 to 2Y8	Data Outputs
24, 25	2G1, 2G2	Output Enable Inputs
36, 35, 33, 32, 30, 29, 27, 26	2A1 to 2A8	Data Outputs
47, 46, 44, 43, 41, 40, 38, 37	1A1 to 1A8	Data Outputs
4, 10, 15, 21, 28, 34, 39, 45	GND	Ground (0v)
7, 18, 31, 42	VCC	Positive Supply Voltage

TRUTH TABLE

INPUTS			OUTPUT
$\overline{G1}$	$\overline{G2}$	An	Yn
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

X : Don't Care
Z : High Impedance

IEC LOGIC SYMBOLS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage (High or Low State) (note 1)	-0.5 to $V_{CC}+0.5$	V
I_{IK}	DC Input Diode Current	-50	mA
I_{OK}	DC Output Diode Current (note 2)	- 50	mA
I_O	DC Output Current	+ 50	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 100	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

1) I_O absolute maximum rating must be observed

2) $V_O < GND$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (OFF State)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to 3.6V)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.7V$)	± 12	mA
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V_{IN} from 0.8V to 2V at $V_{CC}=3.0V$

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value				Unit
		V _{CC} (V)		-40 to 85 °C		-55 to 125 °C		
				Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.7 to 3.6		2.0		2.0		V
V _{IL}	Low Level Input Voltage				0.8		0.8	V
V _{OH}	High Level Output Voltage	2.7 to 3.6	I _O =-100 μA	V _{CC} -0.2		V _{CC} -0.2		V
		2.7	I _O =-12 mA	2.2		2.2		
		3.0	I _O =-12 mA	2.4		2.4		
		3.0	I _O =-24 mA	2.2		2.2		
V _{OL}	Low Level Output Voltage	2.7 to 3.6	I _O =100 μA		0.2		0.2	V
		2.7	I _O =12 mA		0.4		0.4	
		3.0	I _O =24 mA		0.55		0.55	
I _{OZ}	High Impedance Output Leakage Current	2.7 to 3.6	V _I = 0 to 5.5V		± 5		± 5	μA
I _I	Input Leakage Current	2.7 to 3.6	V _I = 0 to 5.5V		± 5		± 5	μA
I _{off}	Power Off Leakage Current	0	V _I or V _O = 5.5V		10		10	μA
I _{CC}	Quiescent Supply Current	2.7 to 3.6	V _I = V _{CC} or GND		20		20	μA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, R_L = 500 Ω, Input t_r = t_f = 2.5ns)

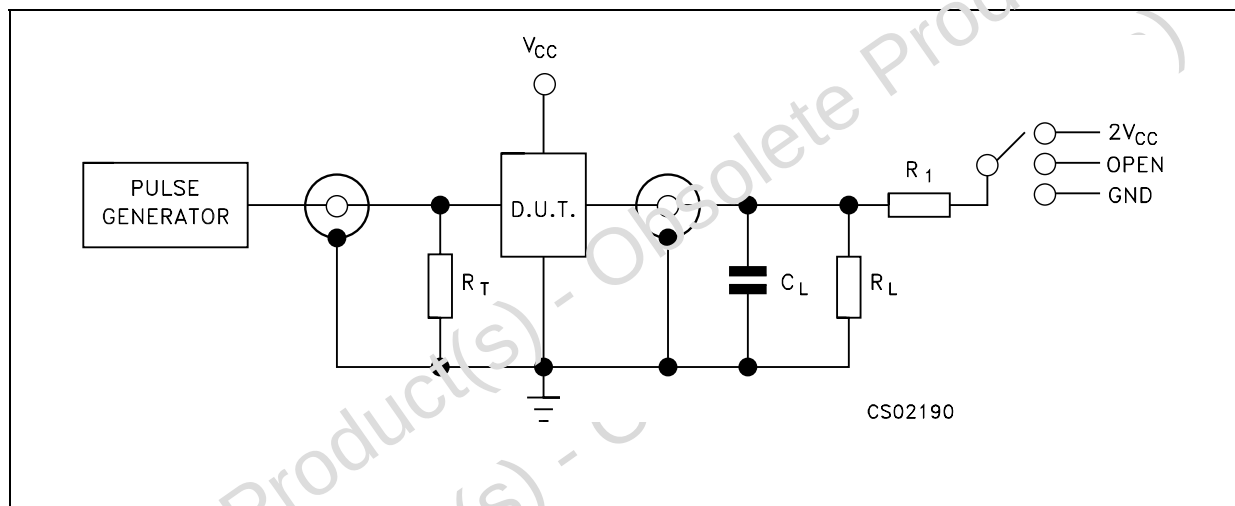
Symbol	Parameter	Test Condition			Value				Unit
		V _{CC} (V)	C _L (pF)		-40 to 85°C		-55 to 125°C		
					Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time A to Y	2.7			1.5	4.7	1.5	4.7	ns
		3.0 to 3.6			1.5	4.1	1.5	4.1	
t _{PZL} t _{PZH}	Output Enable Time	2.7			1.5	5.8	1.5	5.8	ns
		3.0 to 3.6			1.5	4.6	1.5	4.6	
t _{PLZ} t _{PHZ}	Output Disable Time	2.7			1.5	6.2	1.5	6.2	ns
		3.0 to 3.6			1.5	5.8	1.5	5.8	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
C _{IN}	Input Capacitance	3.3	V _I = 0V or V _{CC}		4		pF
C _{OUT}	Output Capacitance	3.3	V _I = 0V or V _{CC}		10		pF
C _{PD}	Power Dissipation Capacitance (note 1) Output enabled	2.5	f _{IN} = 10MHz		45		pF
		3.3	V _I = 0V or V _{CC}		50		
	Power Dissipation Capacitance (note 1) Output disabled	2.5	f _{IN} = 10MHz		3		pF
		3.3	V _I = 0V or V _{CC}		4		

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC1}/16$

TEST CIRCUIT

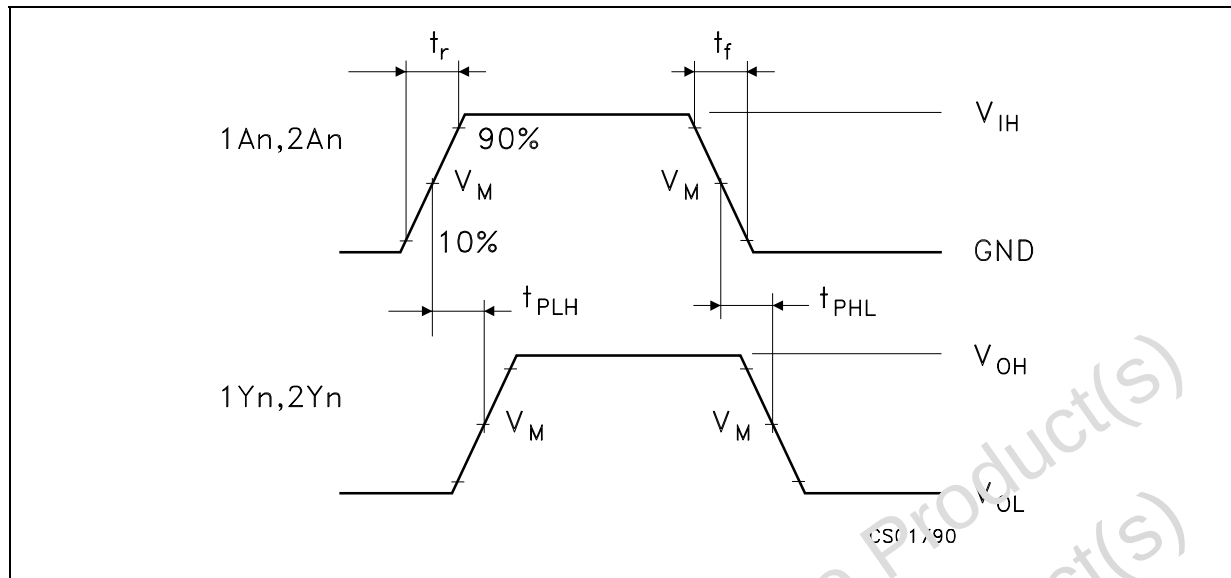
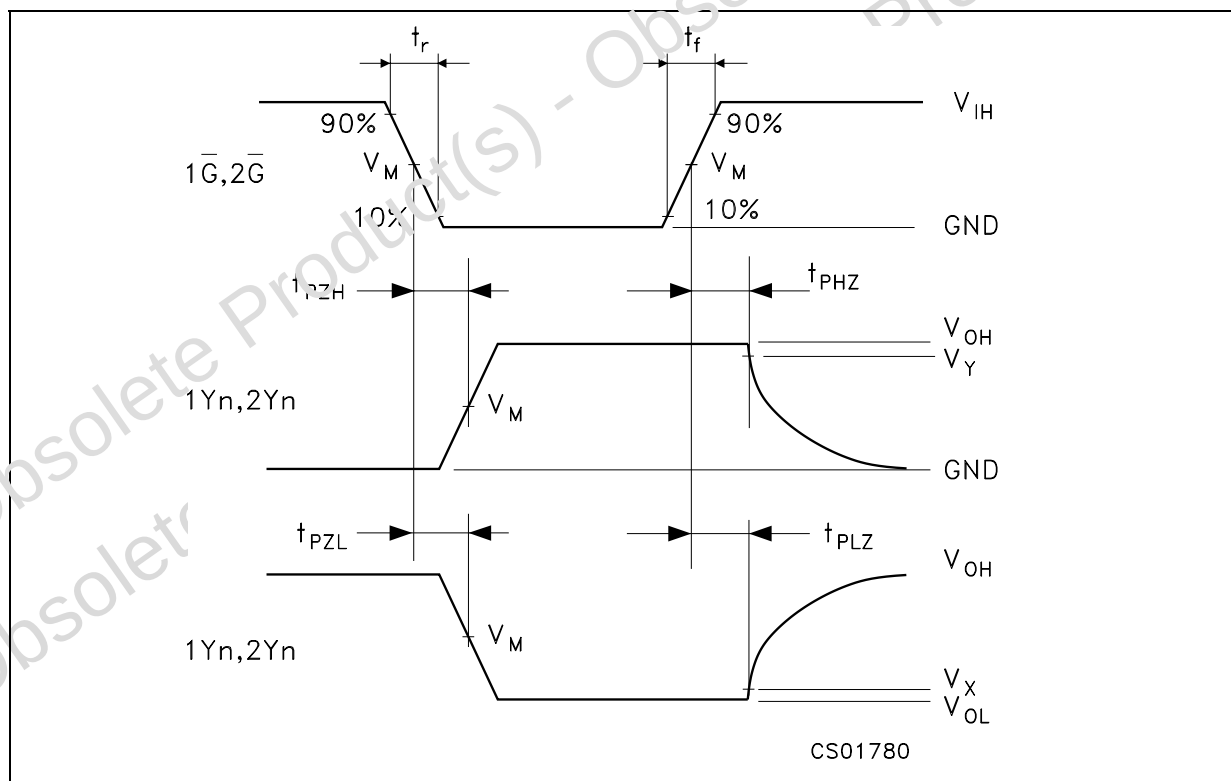


TEST	SWITCH
t _{PLH} , t _{PH}	Open
t _{PZL} , t _{PL}	2V _{CC}
t _{PZL} , t _{PHZ}	GND

C_L = 50 pF or equivalent (includes jig and probe capacitance)

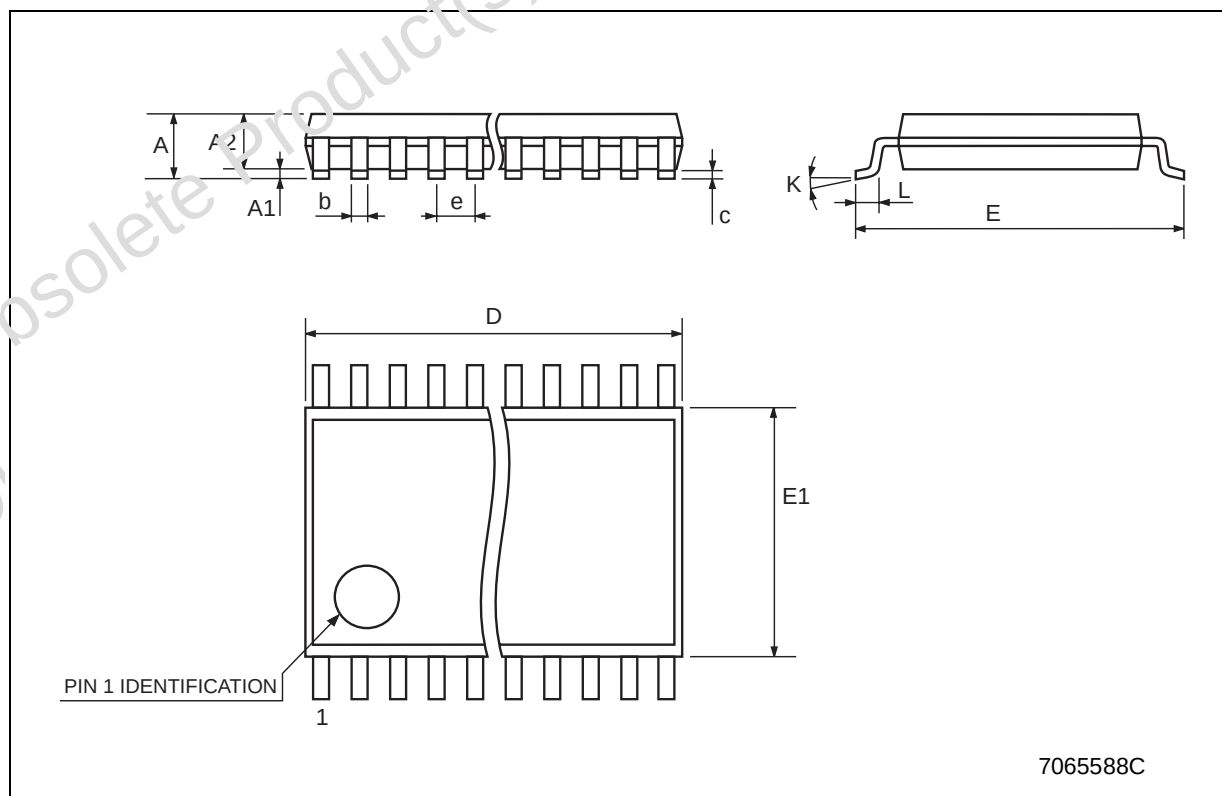
R_L = R₁ = 500 Ω or equivalent

R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)**WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME** ($f=1\text{MHz}$; 50% duty cycle; $V_Y = V_{OH} - 0.3V$, $V_X = V_{OL} + 0.3V$)

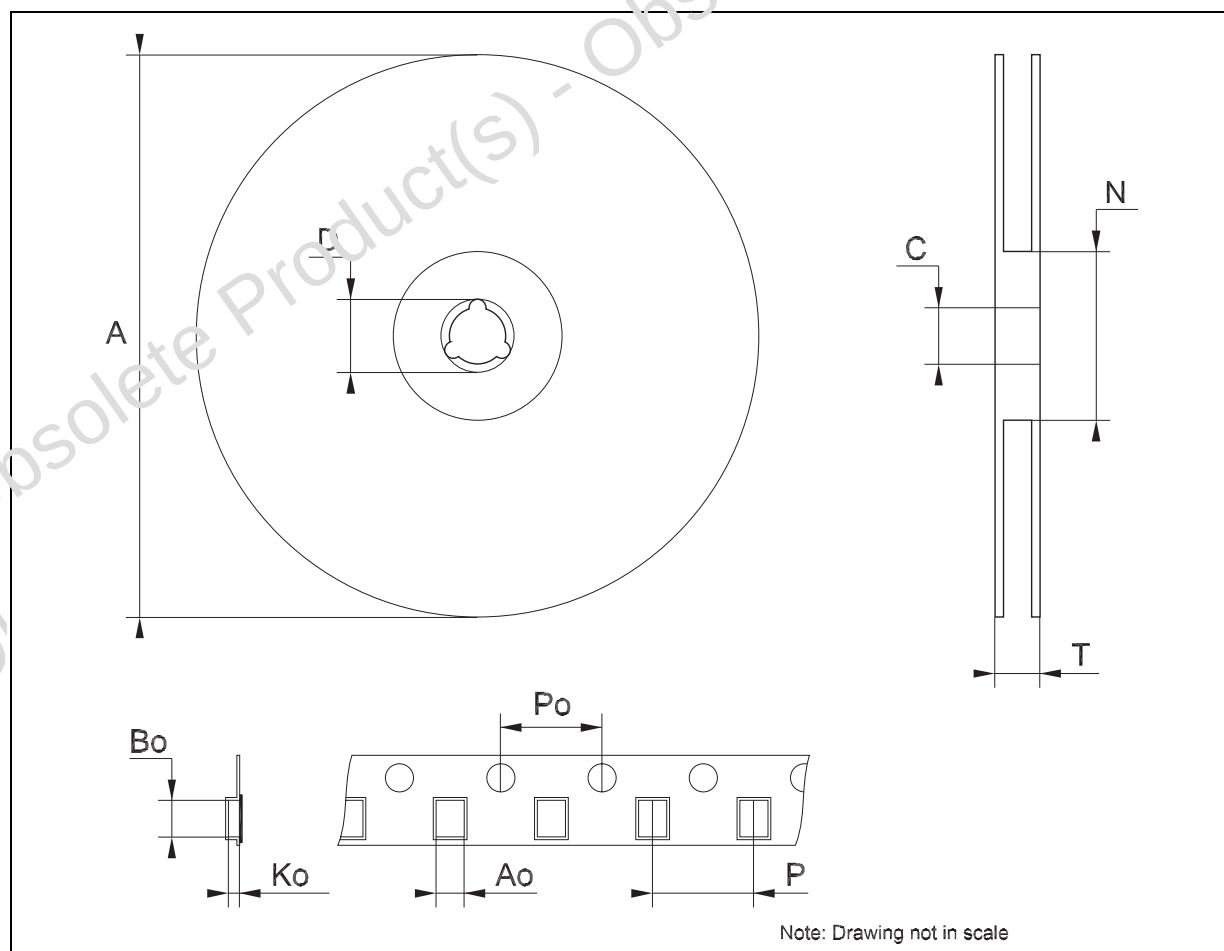
TSSOP48 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002		0.006
A2		0.9			0.035	
b	0.17		0.27	0.0067		0.011
c	0.09		0.20	0.0035		0.0079
D	12.4		12.6	0.488		0.496
E		8.1 BSC			0.318 BSC	
E1	6.0		6.2	0.236		0.244
e		0.5 BSC			0.0197 BSC	
K	0°		8°	0°		8°
L	0.50		0.75	0.020		0.030



Tape & Reel TSSOP48 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			30.4			1.197
Ao	8.7		8.9	0.343		0.350
Bo	13.1		13.3	0.516		0.524
Ko	1.5		1.7	0.059		0.067
Po	3.9		4.1	0.153		0.161
P	11.9		12.1	0.468		0.476



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